

# MUR860F

## 8.0AMPS. GLASS PASSIVATED SUPER FAST RECTIFIERS

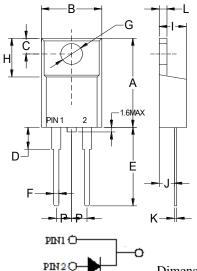
### **FEATURE**

- . Low forward voltage drop
- . High current capability
- . High reliability
- . High surge current capability
- . Epitaxial construction
- . High temperature soldering guaranteed 260°C /10seconds, 0.25"(6.35mm)from case.

#### MECHANICAL DATA

- . Terminal: Plated solderable per MIL-STD 202E, method 208C
- . Case: Molded with UL-94 Class V-0 recognized Flame Retardant Epoxy
- . Polarity: color band denotes cathode
- . Mounting position: any

# <u>ITO-220AC</u>



Dim	Min	Max
A	. 571 (14. 5)	. 610 (15. 5)
В		. 406 (10. 3)
C	. 110 (2. 80)	. 126 (3. 2)
D		. 162 (4. 1)
Е	. 512 (13. 0)	. 551 (14. 0)
F	. 020 (0. 5)	. 031 (0. 78)
G	. 114(2.9)	. 138 (3. 5)
Н	. 268 (6. 8)	. 291 (7. 4)
I	. 162 (4. 1)	. 185 (4. 7)
J	. 110(2.8)	. 126 (3. 2)
K	. 020 (0. 5)	. 028 (0. 7)
L	. 097 (2. 46)	. 113 (2. 86)
P	. 89 (2. 25)	. 113 (2. 85)

Dimensions in inches and (millimeters)

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	SYMBOL	MUR860F	units
Maximum Recurrent Peak Reverse Voltage	$V_{ m RRM}$	600	V
Maximum RMS Voltage	$V_{ m RMS}$	420	V
Maximum DC blocking Voltage	V <sub>DC</sub>	600	V
Maximum Average Forward Rectified Current at $T_C = 100^{\circ}C$	I <sub>F(AV)</sub>	8.0	A
Peak Forward Surge Current 8.3ms single half sine- wave superimposed on rated load (JEDEC method)	$I_{ m FSM}$	120.0	A
Maximum Forward Voltage at 8.0A DC	$V_{ m F}$	2.3	V
Maximum DC Reverse Current $@T_A = 25^{\circ}C$ at rated DC blocking voltage $@T_A = 125^{\circ}C$	I <sub>R</sub>	10.0 400.0	μΑ
Maximum Reverse Recovery Time (Note 1)	$t_{ m rr}$	50	ns
Typical Junction Capacitance (Note 2)	C <sub>J</sub>	60	pF
Typical Thermal Resistance (Note 3)	R <sub>(JC)</sub>	3.2	°C/W
Storage Temperature	$T_{ m STG}$	-55 to +150	°C
Operation Junction Temperature	$T_{ m J}$	-55 to +150	°C

## Note:

- 1. Test Conditions: I<sub>F</sub>=8A, dI<sub>F</sub>/dt=200A/μs
- 2. Measured at 1.0 MHz and applied reverse voltage of 4.0Vdc
- 3. Thermal Resistance From Junction to Case Mounted on Heatsink